



# Dephasing in Strongly Anisotropic Black Phosphorus

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National Enterprise for nanoScience and nanoTechnology

# NEST

# Black phosphorus

Layered structure with orthorhombic symmetry

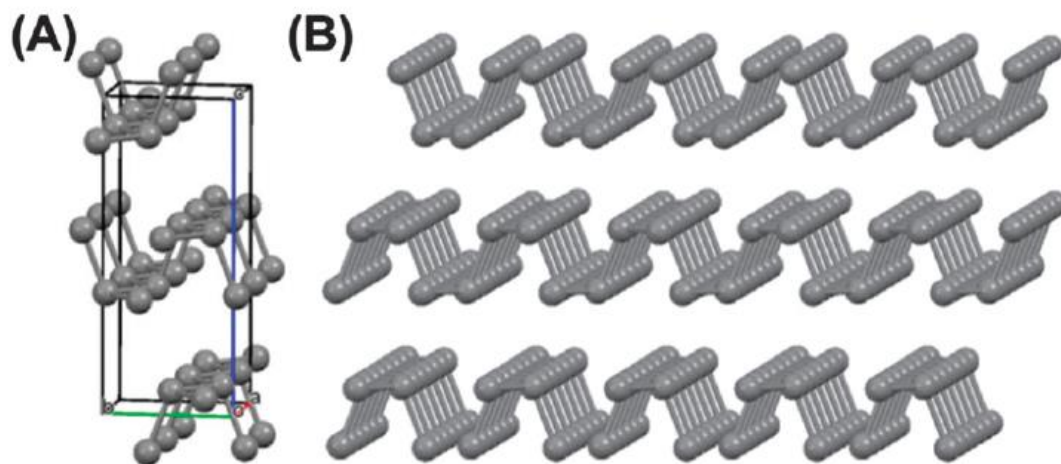
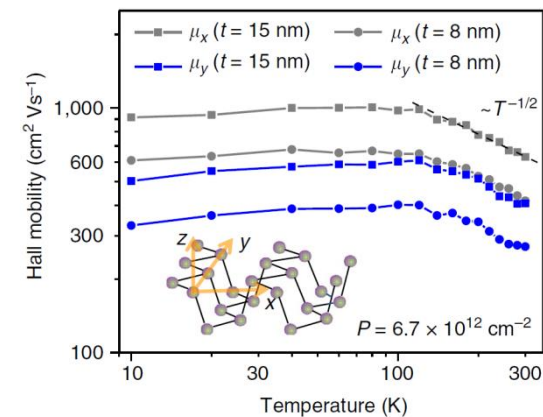
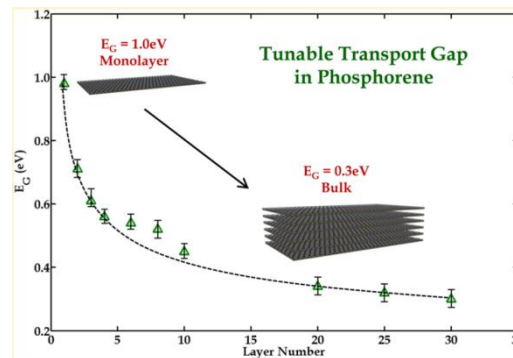
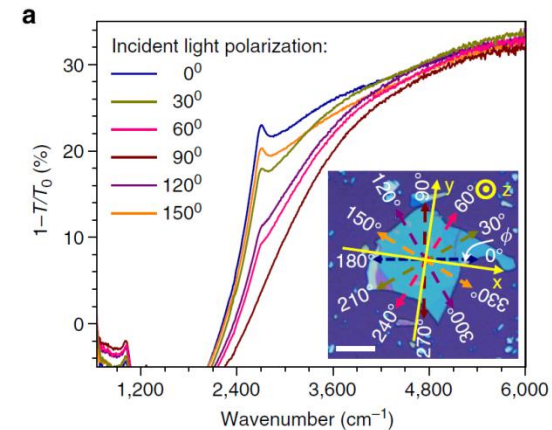
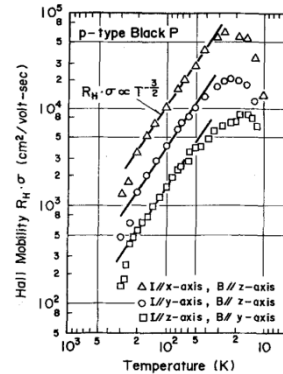


Fig. 1 The chemical structures of the compounds in this study. (A) The orthorhombic unit cell of black phosphorus<sup>19</sup> ( $a = 3.31 \text{ \AA}$ ,  $b = 4.38 \text{ \AA}$ ,  $c = 10.50 \text{ \AA}$ ,  $\alpha = \beta = \gamma = 90^\circ$ ; space group  $Bmab$ ; Crystallography Open Database ID: 1010325) which generates a layer structure comprising corrugated lamellae of phosphorus atoms held together by weak interlayer forces. (B) Three-layer phosphorene.

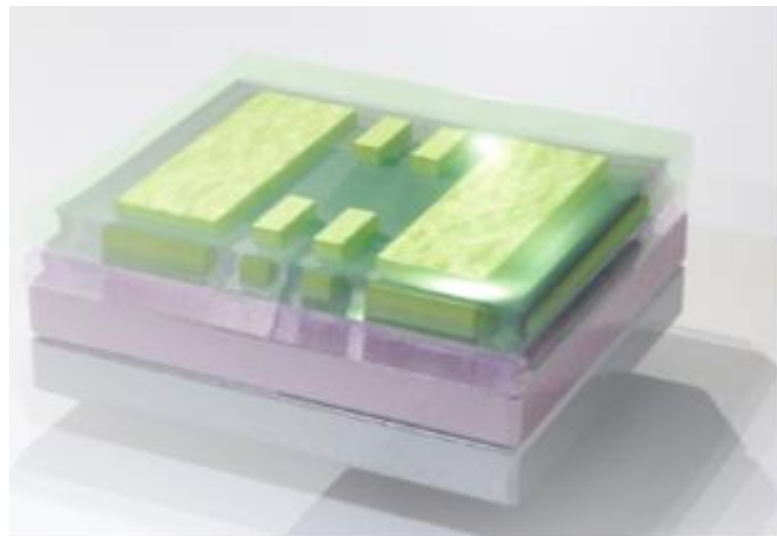
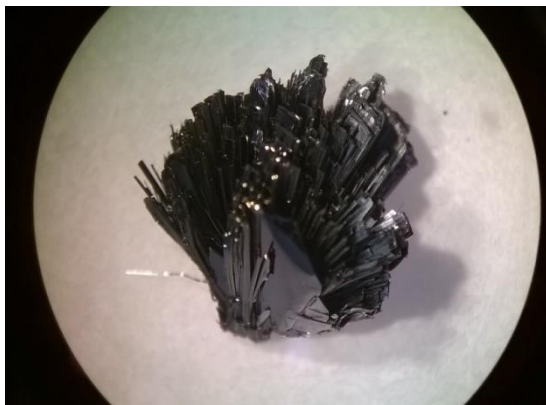
Cell parameters  
 $a=3.13\text{\AA}$   
 $b=10.47\text{\AA}$   
 $c=4.37\text{\AA}$

# The renaissance of black phosphorus

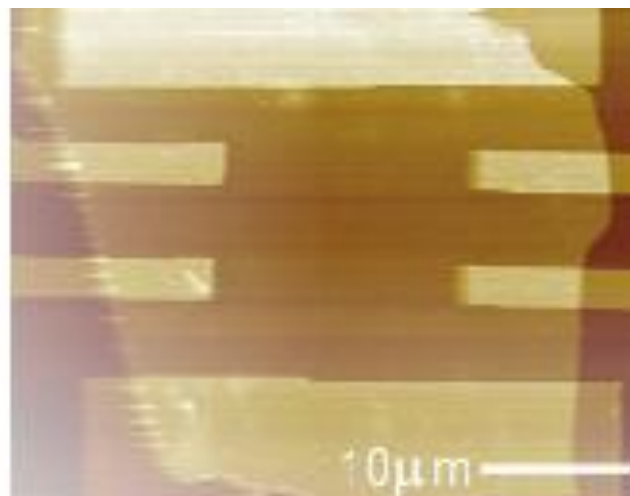
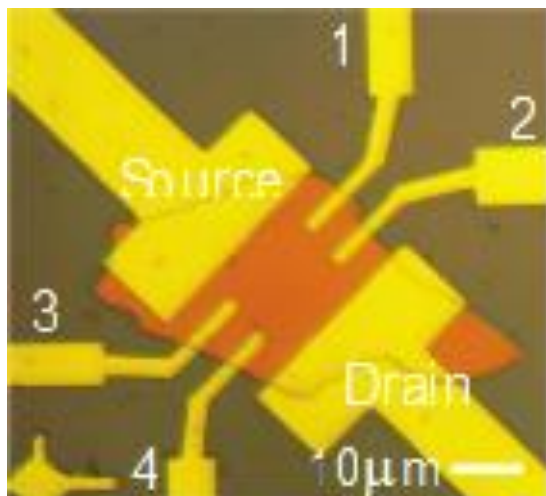
- ✓ In 1914 first successful synthesis (Bridgman) and in 2007 synthesis at room pressure (Lange, Nilges)
- ✓ p-type semiconductor: 0.3eV direct band gap and high hole mobility (64,000 cm<sup>2</sup>/Vs @ 20 K)
- ✓ 1983 (Narita): n-type doping by Te
- ✓ 2014: First publications on bP layered thin films
- ✓ Highly reactive in air
- ✓ Band-gap tunable with layer number
- ✓ **In-plane anisotropy** of optical and transport properties
- ✓ ... and much more! SdH, QH...



# bP Field Effect Transistor



PMMA  
MMA  
Ti/Au contacts  
bP flake  
HMDS  
SiO<sub>2</sub> thermal oxide  
Si

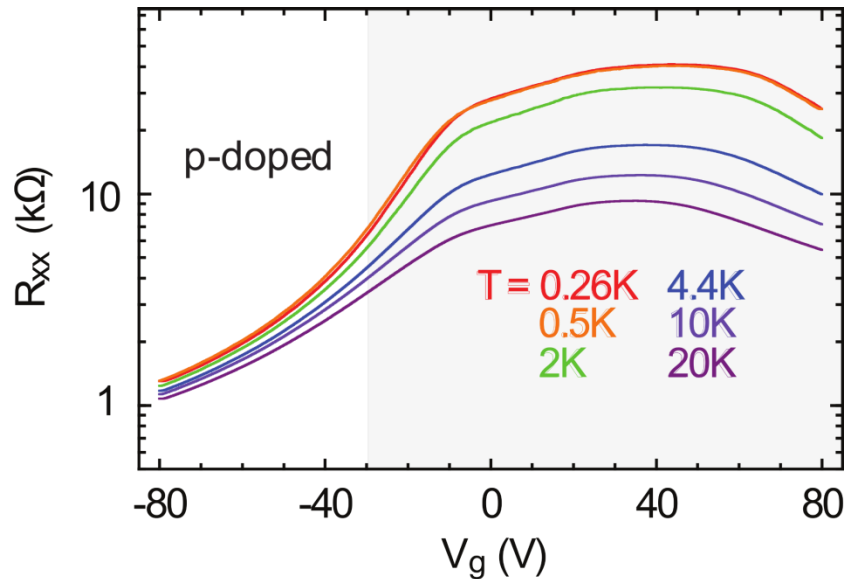


$R_{xx}$ : 1-2

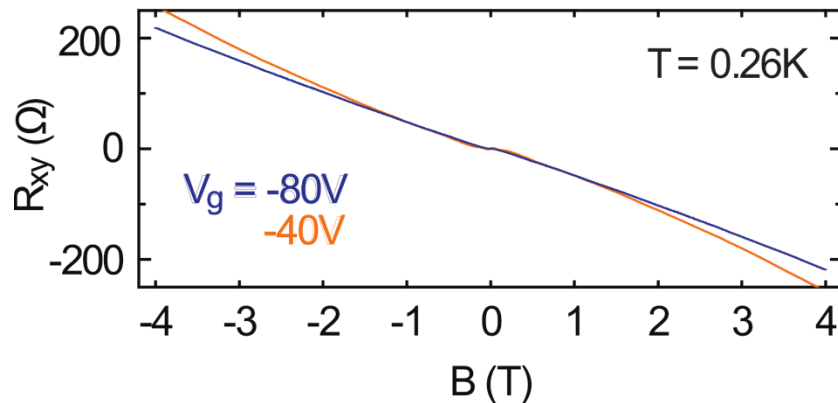
$R_{xy}$ : 1-3

Flake thickness:  
 $65 \pm 2$  nm

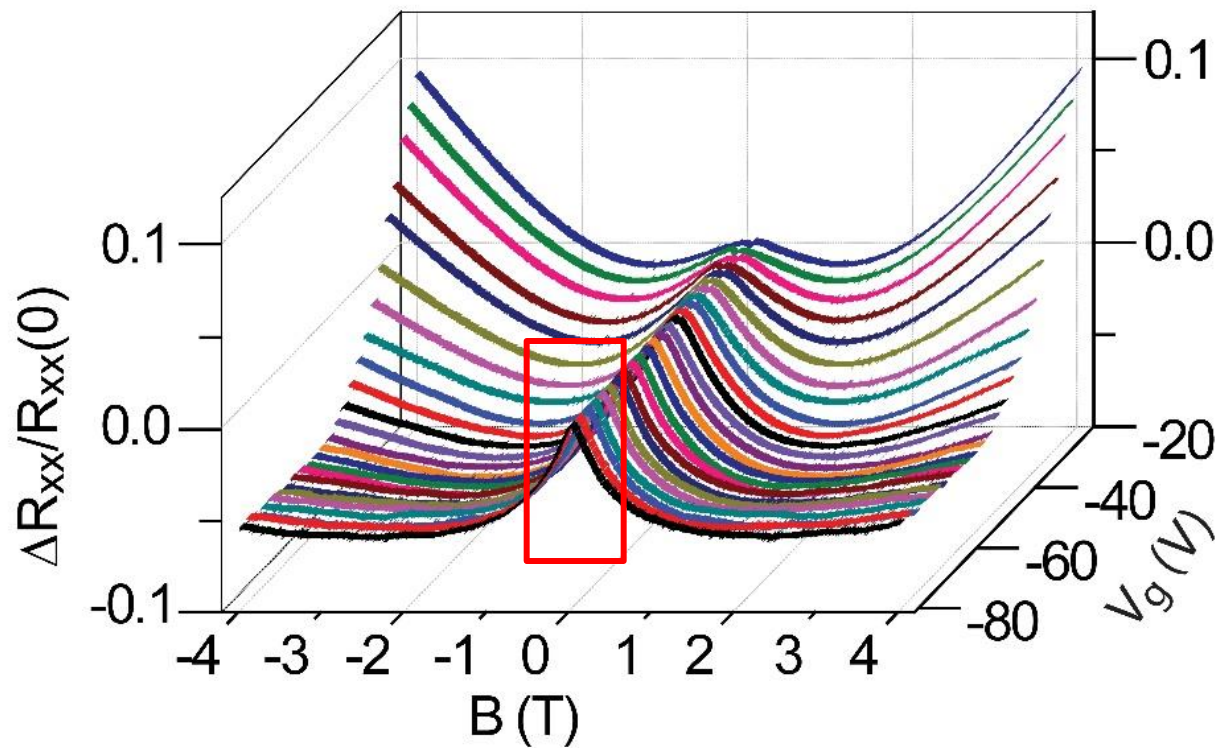
# Transport Characterization



- $\rho \sim V_g$  for  $V_g < -30$  V
- $\rho = 10^{13}$  cm<sup>-2</sup> for  $V_g = -30$  V
- Field-effect mobility  $\mu$ :  
300 cm<sup>2</sup>/Vs at  $V_g = -70$  V
- Negligible T-dependence in  $\mu$   
for 0.26 K < T < 20 K

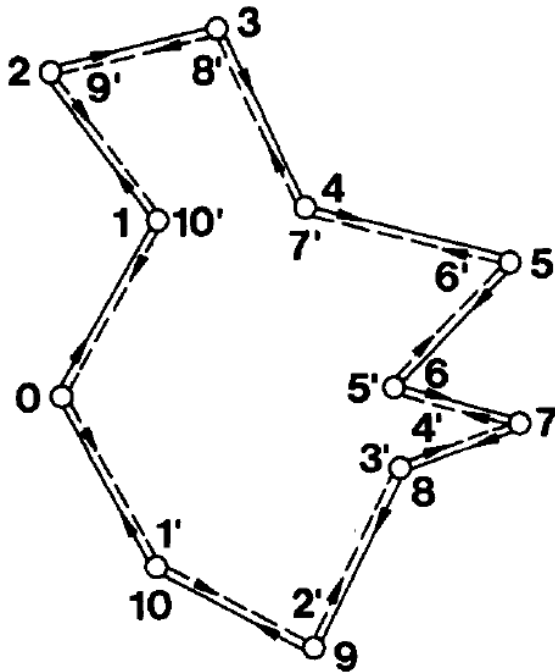


# Longitudinal magnetotransport measurements



# Weak Localization

Weak localization is a quantum effect related to coherent scattering at low temperatures.



Amplitude  $A_1$



Amplitude  $A_2$

Normal Diffusion Model:

$$P = |A_1|^2 + |A_2|^2 = 2 |A|^2$$

Coherent Addition:

$$P = |A_1 + A_2|^2 = |2A|^2 = 4 |A|^2$$

Since weak localization is a coherent scattering effect:

- It's depressed by magnetic field
- It's smeared by temperature

Picture from Bergmann, Weak localization in thin films, Physics Reports 107, 1984

# Weak Localization

$$\Delta\sigma = -\frac{e^2}{2\pi^2\hbar} \left( \Psi \left( \frac{1}{2} + \frac{B_1}{B} \right) - \Psi \left( \frac{1}{2} + \frac{B_2}{B} \right) + \frac{1}{2} \Psi \left( \frac{1}{2} + \frac{B_3}{B} \right) - \frac{1}{2} \Psi \left( \frac{1}{2} + \frac{B_2}{B} \right) \right), \quad (1)$$

where  $\Psi$  is the digamma function. The field parameters in the above expression are given by:

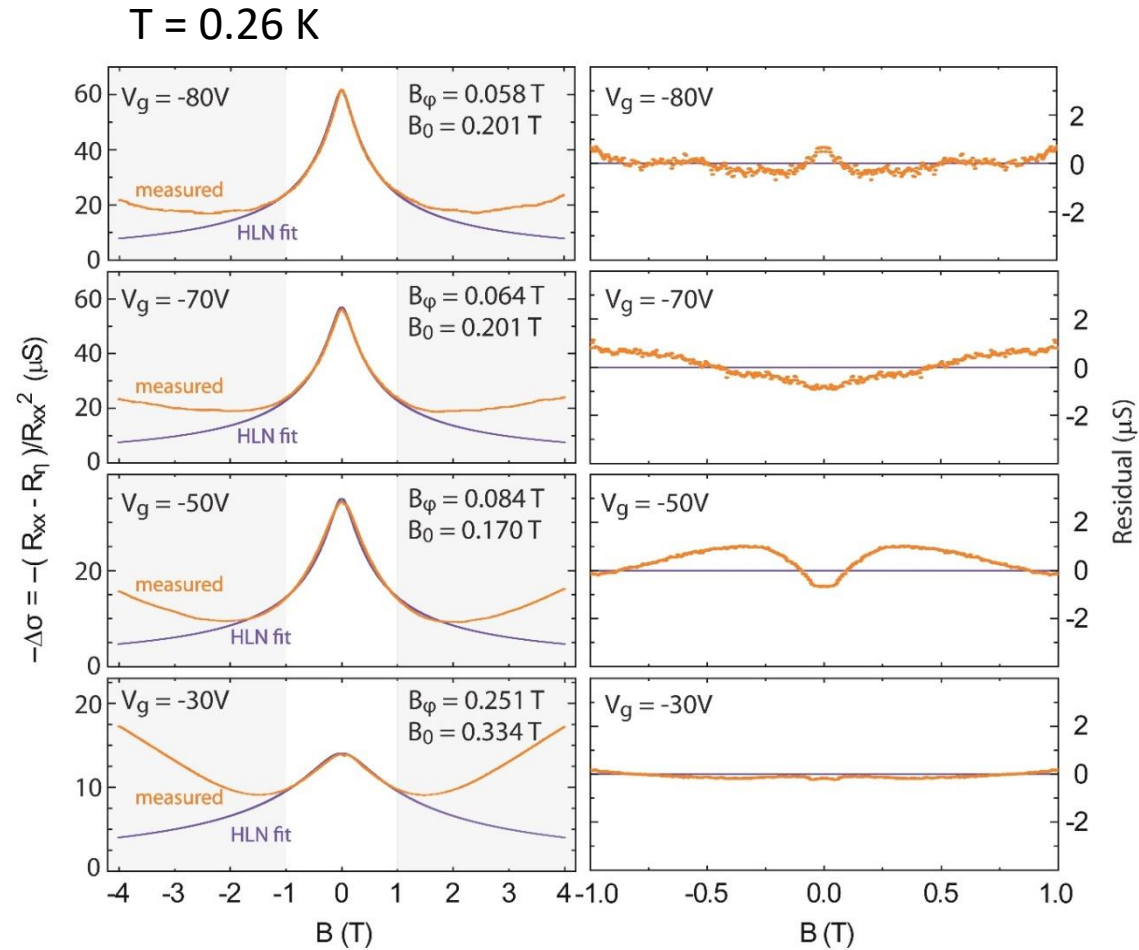
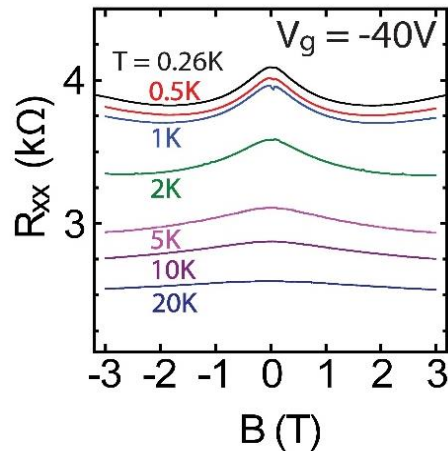
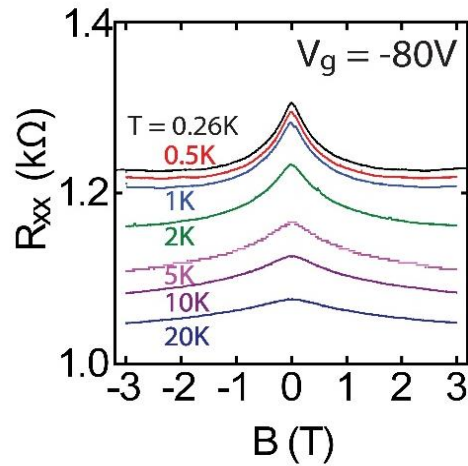
$$B_1 = B_0 + B_{so} + B_s \quad (2)$$

$$B_2 = \frac{4}{3} B_{so} + \frac{2}{3} B_s + B_\phi \quad (3)$$

$$B_3 = 2B_s + B_\phi \quad (4)$$

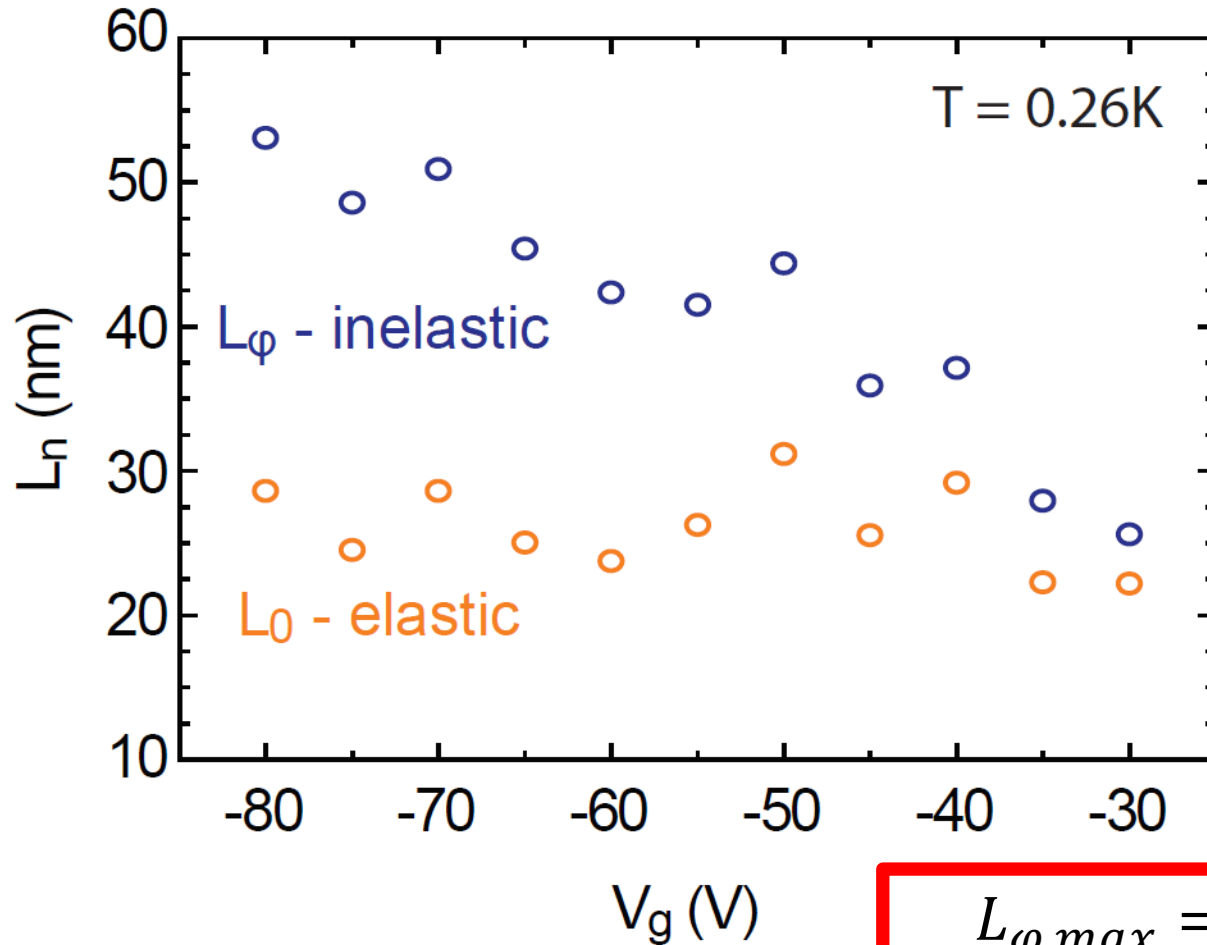


# Weak Localization



# Scattering Lengths

$$BL^2 = h/4e$$



$L_{\phi,max} = 55\text{ nm}$

# Scattering Lengths

- Ballistic transport:  $\tau_\varphi \propto T^{-2}$
- Diffusive transport ( $\tau_0 < \tau_\varphi$ ):

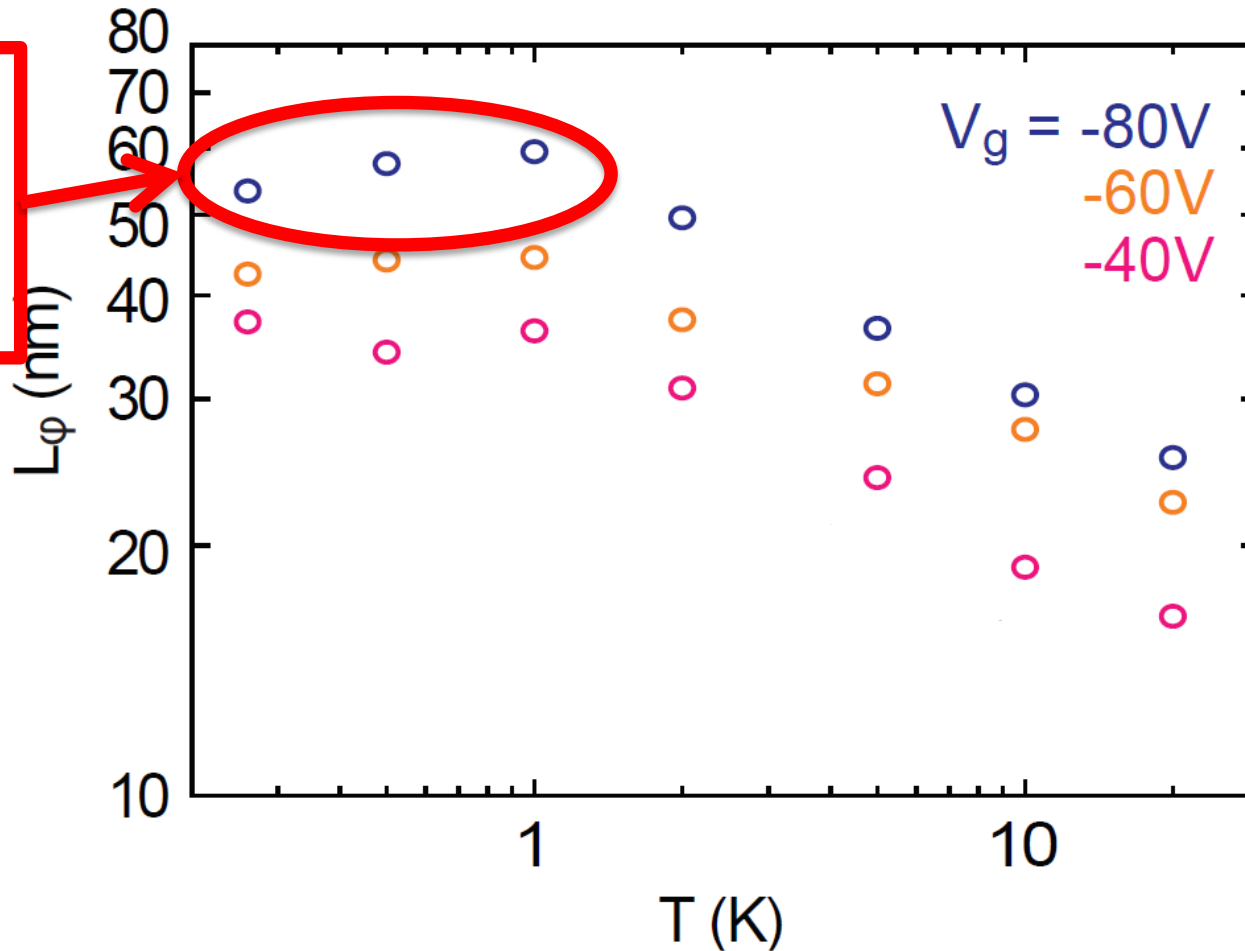
Dephasing length vs. inelastic scattering time:

$L_\varphi = \sqrt{D\tau_\varphi}$  with  $D$  diffusion coefficient

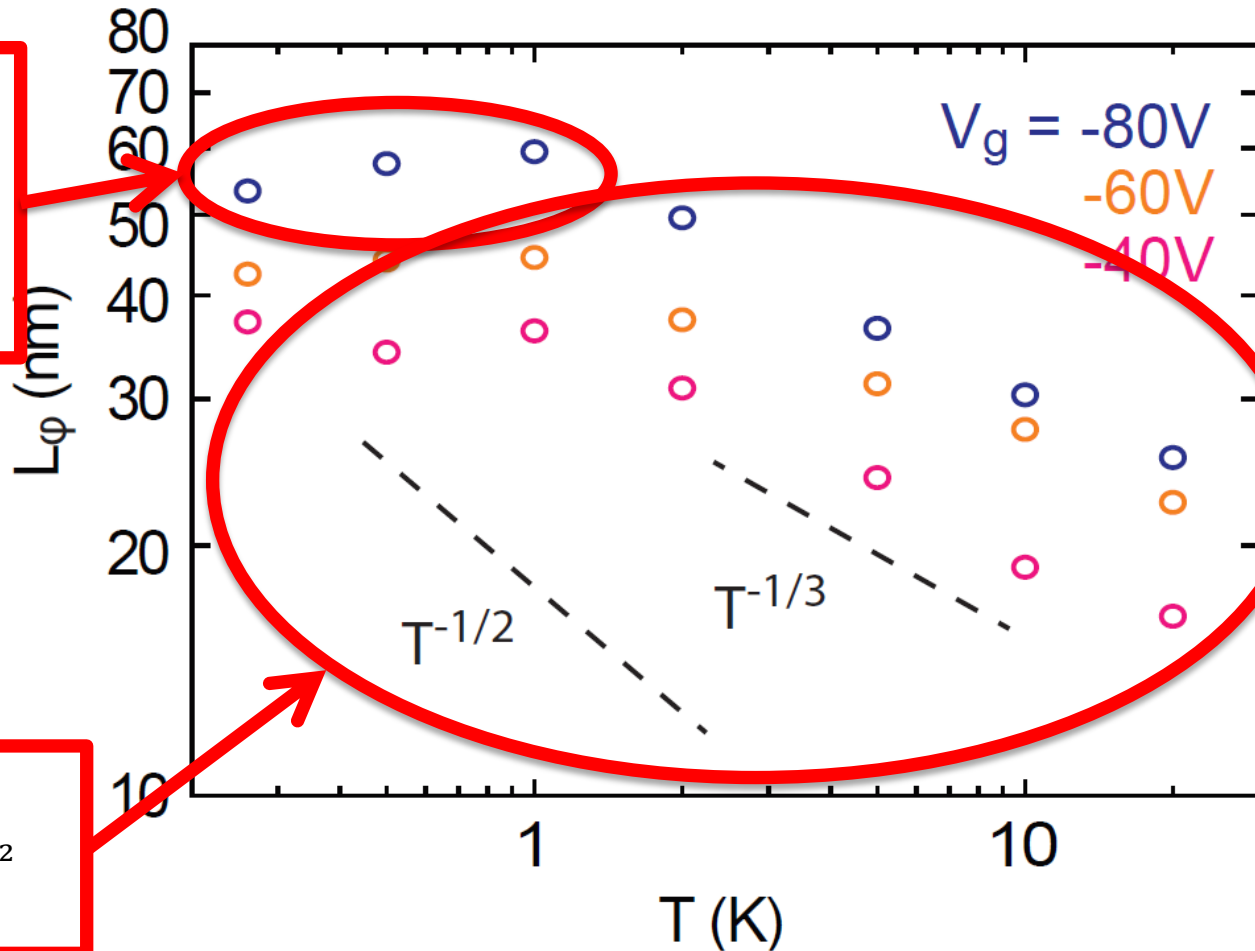
$$\tau_\varphi \propto T^{-1} \quad \text{or} \quad L_\varphi \propto T^{-1/2}$$

# Scattering Lengths

Saturation most likely due to dynamical impurities.



# Scattering Lengths



Saturation most likely due to dynamical impurities.

$L_\phi$  does not follow a  $T^{-1/2}$  behaviour.

## Geometry-Dependent Dephasing in Small Metallic Wires

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(Received 19 June 2000)

Temperature dependent weak localization is measured in metallic nanowires in a previously unexplored size regime down to width  $w = 5$  nm. The dephasing time,  $\tau_\phi$ , shows a low temperature  $T$  dependence close to quasi-1D theoretical expectations ( $\tau_\phi \sim T^{-2/3}$ ) in the narrowest wires, but exhibits a relative saturation as  $T \rightarrow 0$  for wide samples of the same material as observed previously. As only sample geometry is varied to exhibit constraint on models of dephasing

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## Phase-coherent transport in ropes of single-wall carbon nanotubes

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(Received 21 May 2001; revised manuscript received 23 July 2001; published 6 September 2001)

To study the phase breaking scattering events in single-wall carbon nanotubes (SWNTs), ropes of SWNTs are intentionally damaged by  $\text{Ar}^+$  ion milling. Due to this treatment, the average distance an electron can travel before being elastically scattered is reduced to about 10 nm. This significantly increases the probability of one-dimensional localization and allows us to obtain the phase coherence length ( $L_\phi$ ) in ropes of SWNTs as a function of temperature. We find that Nyquist scattering ( $\tau_\phi \sim T^{-2/3}$ ) as well as another dephasing mechanism with a  $\tau_\phi \sim T^{-1}$  dependence are involved in limiting the phase-coherent transport. We also investigate the scattering of hot electrons in the system. The results support the statement that two different scattering mechanisms dominate the phase coherence length for different rope samples.

# Comparison with quasi-1D wires

D. Natelson et al.  
PRL 86 (2009):

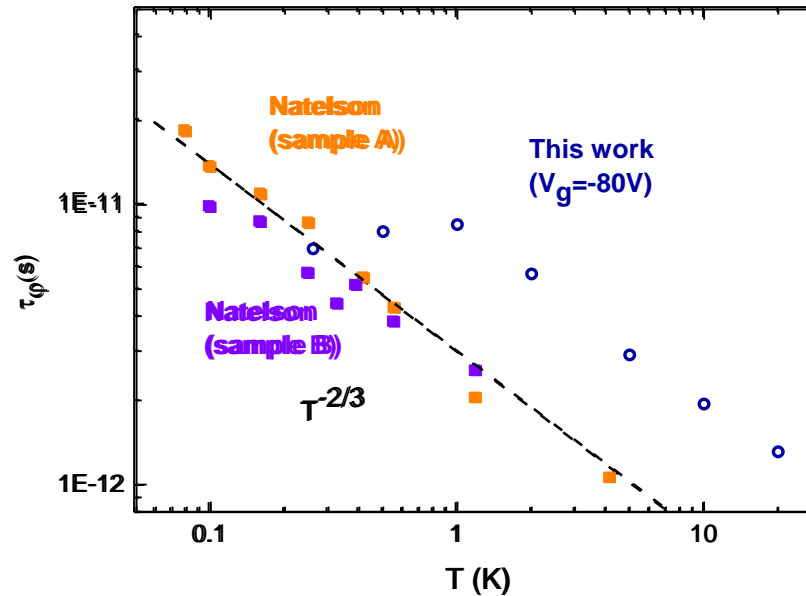
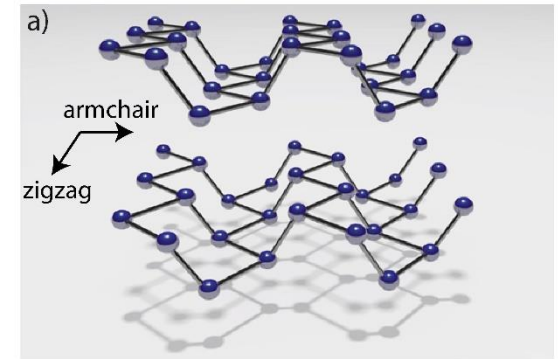
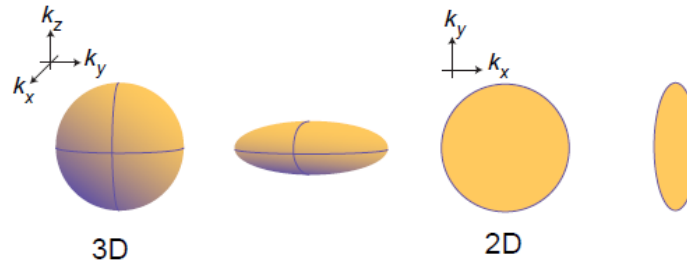
quasi-1D:

$$L_\varphi, L_T > w, t$$

width  $w$   
thickness  $t$

$$\tau_\varphi \propto T^{-2/3}$$

$$L_\varphi \propto T^{-1/3}$$



$$L_\varphi = 55 \text{ nm}$$

thermal length:

$$L_T = \sqrt{\hbar D / k_B T} = 10 - 60 \text{ nm}$$

# Conclusions

- ✓ Weak localization observed in a bP FET
- ✓ Excellent agreement with HLN model
- ✓ Dephasing length  $L_\varphi$  reaches 55 nm
- ✓ T-dependence of  $L_\varphi$  close to quasi-1D
- ✓ We attribute this to strong in plane anisotropy of bP





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# Funding



SEED project